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Tin Whisker Electrical Short Circuit Characteristics - Part I

Karim J. Courey, Shihab S. Asfour, Jon A. Bayliss, Lawrence L. Ludwig, and Maria C. Zapata

Abstract—Existing risk simulations make the assumption that when a free tin whisker has bridged two adjacent exposed electrical conductors, the result is an electrical short circuit. This conservative assumption is made because shorting is a random event that has a currently unknown probability associated with it. Due to contact resistance electrical shorts may not occur at lower voltage levels. In this experiment, we study the effect of varying voltage on the breakdown of the contact resistance which leads to a short circuit. From this data we can estimate the probability of an electrical short, as a function of voltage, given that a free tin whisker has bridged two adjacent exposed electrical conductors. In addition, three tin whiskers grown from the same Space Shuttle Orbiter card guide used in the aforementioned experiment were cross-sectioned and studied using a focused ion beam (FIB).

Index Terms—Tin Whiskers, Contact Resistance, Short Circuit, FIB (Focused Ion Beam).

I. INTRODUCTION

METAL whiskers are filamentary growths which may develop on metal surfaces [1]. Metal whiskers usually erupt from thin metal films that have been deposited on a

substrate, and can grow in a variety of shapes including, straight, kinked, and curved [2]. Metal whiskers have grown on different metal films. Although a number of metal coatings have exhibited a propensity for whisker growth, the metal films that are most often referred to in the metal whisker literature are cadmium [3], zinc and tin [4]. Tin films deposited by electroplating are more prone to whiskering than hot dipped coatings [5].

The physical dimensions of tin whiskers also exhibit a great deal of variability. Tin whisker diameters can range from 0.006 μ m to 10 μ m [6]. They can also grow up to 18mm in length [7].

The maximum current that a whisker can carry before fusing open has been measured up to 10mA for whiskers with a 1 μ m diameter, up to 30 mA for whiskers with a 2.5 μ m diameter, and up to 75mA for whiskers with a 4 μ m diameter [8]. Given the current-carrying capacity and the length that whiskers can grow, the potential for short circuits in electronics is a very real concern.

The failure modes caused by tin whiskers can be grouped into four different categories. The failure modes include: permanent short circuits in low current applications, transient short circuits in applications where current is high enough to cause the whisker to fuse open, metal vapor arcing in a vacuum, and debris/contamination resulting from vibration which frees loose whiskers that can interfere with optical surfaces or bridge exposed electrical conductors [9].

Metal whisker failures can be categorized by application into commercial satellite, military, medical, industrial/power, and computers [10]. These failures include heart pacemakers [11], apnea monitors [12], a nuclear reactor shutdown [13], computers in data centers with raised flooring [14], F-15 Radar Problems [15], Patriot Missile [16], in addition to a number of commercial satellites. After reviewing the aforementioned failures, it is evident that whiskers can pose serious problems in high reliability systems that could result in loss of life as well as significant capital losses.

Electronics have traditionally used tin plating on leads to increase solderability and to prevent corrosion of the base metal [17]. Since the 1960's alloying the tin plating with as little as 1% lead has proven to be an effective tin whisker mitigation strategy while maintaining desirable qualities such as good solderability, low cost, appearance, and ease of plating process control [18]. However, errors in process controls have allowed pure tin plating to slip through the supply chain even

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when it was prohibited by procurement specifications. Process escapes have resulted in tin whisker related failures, for example the relay used in military aircraft that failed due to metal vapor arcing caused by tin whisker shorts [19]. In addition, in an effort to protect the environment, lead-free legislation such as the European Union's Reduction of Hazardous Substances (RoHS) has placed restrictions on the use of lead, and other hazardous materials [20]. To comply with RoHS, and other lead-free legislation, many manufacturers have converted to pure tin finishes. Given that the spacing between leads in electronics continues to decrease as well as the proliferation of pure tin finishes, improving our ability to assess the risk associated with tin whiskers remains an important area of study.

II. BACKGROUND

An application-specific tin whisker risk algorithm was developed by Pinsky of Raytheon in 2003 [21]. This risk assessment considers the following factors: conductor spacing, lead content in tin plating, process by which the tin was deposited, tin thickness, material directly beneath the tin, substrate controlling the coefficient of thermal expansion, thermal treatments the tin was subjected to after deposition, conformal coating over the tin, use of mechanical hardware, vulnerability of the system to dysfunction as a result of the presences of small pieces of conductive contaminants, use of conformal coating on conductors in the enclosure, and air flow in the assembly. The purpose of this algorithm was to quantify the risk that tin whiskers will bridge between conductors for a specific tin plating application.

In 2005, Hilty and Cormann of Tyco Electronics developed a monte carlo simulation tin whisker reliability assessment [22]. The purpose of their work was "to help predict the likelihood for electrical shorting between adjacent leads of a typical component". Tin whiskers were grown on two different samples. The first was a plating and substrate selection that had been proven to grow whiskers; the second utilized a plating process and substrate shown to mitigate whisker growth. After exposing both of these samples to the same accelerated aging environment, the quantity, length, and growth density were measured. This data was used to fit the statistical distributions that were utilized by the simulation to determine whisker length. The locations of the whiskers, the rotation and inclination angles were randomly generated in the simulation. Whiskers that were long enough and grew at an angle that allowed them to touch an adjacent contact were identified as a failure for the component. The results of the simulations provide a quantitative assessment of the effectiveness of plating process mitigation in reducing simulated failure rates, as well as the effect of terminal separation distance. This was the first application of a monte carlo simulation for tin whisker risk assessment.

In October 2005, the second tin whisker risk assessment using monte carlo simulation was published by Fang at the

University of Maryland [23]. In addition to developing a simulation to predict the risk of an electrical short from a tin whisker growth from a conductor to an adjacent conductor, this study also developed a simulation to assess the risk of shorts from free whiskers. The author attributed the large difference between the experimental results and the results of the simulation for free whiskers to contact resistance. In the recommendations for future work section, Dr. Fang stated "In order to obtain a more accurate simulation answer, it is recommended to quantify the probability of occurrence of an electrical short given a whisker bridging adjacent exposed conductors physically. This number will be used as an input data to the algorithm to correct the final bridging simulation risk".

In the aforementioned simulations it is assumed that physical contact between a whisker and an exposed contact results in an electrical short. This conservative assumption has been made because the probability of an electrical short from tin whiskers has not yet been determined. The purpose of our experiments was to quantify the probability of an electrical short when a whisker bridges two adjacent exposed electrical contacts.

Contact resistance is the sum of the constriction resistance and the film resistance [24]. When two surfaces touch, only a small portion of the area actually makes contact due to unevenness in the surfaces. The a-spot is the radius of the circular contact area. Current flow is constricted through the smaller area resulting in a constriction resistance. Film resistance is due to the build up of tarnish films (oxides, etc.) on the contact surfaces that act in a nearly insulating manner.

Slade [25] points out that when the ratio of $(\rho_f / \rho)(d/a)$ is much larger than unity, the effect of constriction resistance is overshadowed by the film resistance, where ρ_f = the resistivity of the film, ρ = the resistivity of the substrate material, d = the film thickness, a = the a-spot radius.

Contact resistance can be measured by putting two metal cylinders in contact with each other in a crossed arrangement under a mechanical load, and measuring the current through the crossed rods and the voltage across the crossed rods [26]. The a-spot radius can be estimated with the crossed cylinder model developed by Holm as shown in equation 1.1. This assumes that the whiskers are cylindrical which is a simplification since whiskers are fluted.

$$a = 1.11 \sqrt[3]{(P/E)r} \quad (1.1)$$

In Equation 1.1 P = the mechanical load, E = the modulus of elasticity, r = the radius of crossed rods and a = the radius of the contact surface [26]. The tip of the micromanipulator which is used to make contact with the tin whiskers is also called the probe. The mechanical load of the probe touching the whisker can be estimated by modeling the whisker as a cantilever beam as shown in Figure 1.

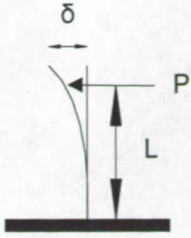


Fig. 1. Cantilever beam whisker model illustrating the mechanical load placed on a whisker by the micromanipulator probe.

The whisker bending model also assumes that the whiskers are cylindrical. With that assumption stated, P = the force applied to the whisker, L = the distance from the base of the whisker to the applied force, δ = the whisker deflection, I = the moment of inertia, and E = the modulus of elasticity [27].

$$P = \frac{3EI\delta}{L^3} \quad (1.2)$$

The moment of inertia for a circular section is shown in equation 1.3 [27].

$$I = \frac{\pi r^4}{4} \quad (1.3)$$

If we assume a whisker has a diameter of 2 μm , length of 4mm, the probe contacts the whisker at 80% of its length (L = length of whisker $\times$ 0.80), and it deflects 5% of its length (δ = length of whisker $\times$ 0.05), then using equation 1.3 the moment of inertia $I = 7.854 \text{ E-}25 \text{ m}^4$. Given that the modulus of elasticity for tin is $E = 41.369 \text{ GPa}$ [28], using equation 1.2, the force applied to the whisker $P = 5.949\text{E-}10 \text{ N}$. Since we have calculated a value for P , we can determine the spot area radius using equation 1.1, resulting in the value $a = 2.689\text{E-}9\text{m}$.

Since the resistivity of tin at 20°C is $\rho = 11.6\text{E-}8 \text{ }\Omega\text{m}$ [25], and the resistivity of tin oxide at 20°C is $\rho_{\text{oxide}} = 4\text{E}4 \text{ }\Omega\text{m}$ [29], if we assume the oxide film thickness is $d = 50\text{\AA}$ [30], the ratio of $(\rho_f / \rho)(d/a) = 6.412\text{E}11$. Since the aforementioned ratio is much larger than unity, we can conclude the effect of constriction resistance is overshadowed by the film resistance.

In order to determine the probability of an electrical short from a tin whisker across adjacent exposed leads it is necessary to determine when the film resistance from the oxide layer and any other films breaks down. Conduction can be experienced when the film is ruptured mechanically in some spots, as in switch with wiping action contacts, or is electrically broken down when enough voltage is applied. This type of breakdown is called fringing [24]. The breakdown voltage can be seen by examining change in the plots of the whisker voltage and whisker current.

III. EXPERIMENTAL PROCEDURES

To determine the break down voltage a micromanipulator probe was brought in contact with the side of a tin whisker growing from a tin-plated beryllium copper card guide as illustrated in Figure 2. The card guide used in this experiment was removed from a Space Shuttle Orbiter Flight Control System (FCS) Ascent Thrust Vector Control (ATVC) Line Replaceable Unit (LRU) that was built in 1989.

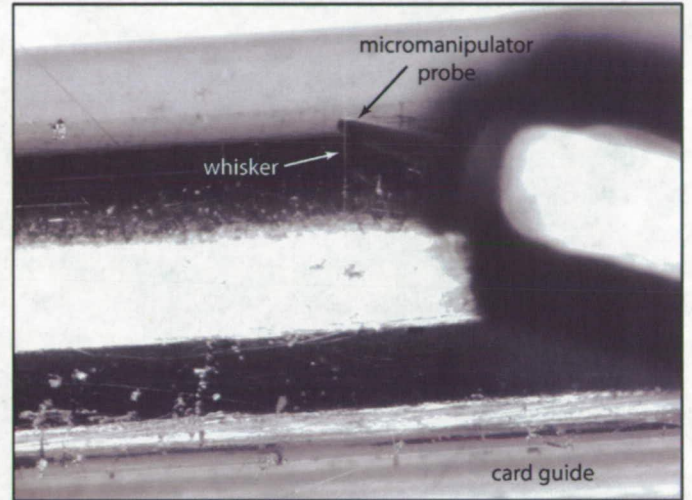


Fig. 2. The micromanipulator probe touching tin whisker number 20 growing from the card guide.

A PXI automated data acquisition (DAQ) system was used to ensure improved experimental control. PXI is a platform for measurement and automated systems that uses a PC (Personal Computer) [31]. The acronym PXI stands for (PCI eXtensions for Instrumentation). Peripheral Component Interconnect (PCI) is a specific type of bus that is used in PC's for connecting peripheral devices to the motherboard of the PC [32].

DAQ software was written using LabVIEW® to automate both the incrementing of power supply voltage changes as well as the gathering of the voltage and current data for each of the tin whiskers. Once contact was established, as determined with an optical microscope, the power supply voltage was increased from 0 to 45 vdc in 0.1 vdc increments. Reference Figure 3.

Automated Tin Whisker Test Fixture

PXI instrumentation running a Labview program

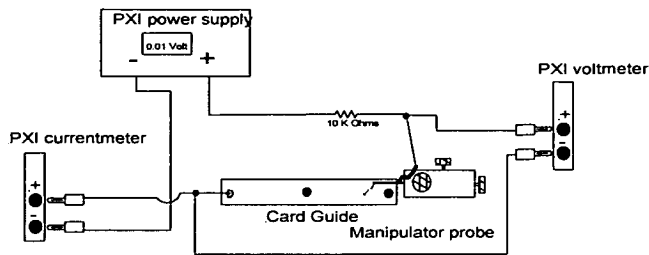


Fig. 3. Cable interconnect diagram for the tin whisker test station instrumentation.

The software captured 3 to 4 samples per second over the entire voltage range. The whisker voltage measurement included the resistance of the micromanipulator probe and lead as well as the card guide. However the resistance of the whisker prior to film breakdown is so high, and the lead/probe resistance and the card guide are so low, that they can be represented as a single resistance value, R_2 = Whisker Resistance, in the simplified electrical schematic illustrated in Figure 4. To avoid vaporizing the whiskers, a 10 K Ω resistor was placed in series with the whisker to limit the current through the whisker when the break down voltage was achieved. With the current-limiting resistor in place, the test station was limited to a maximum of 4.5 mA at 45 vdc. The automated test fixture was validated by substituting a calibrated resistor decade box for the micromanipulator, whisker and card guide. The experiment was repeated to develop an empirical probability distribution of shorting as a function of voltage.

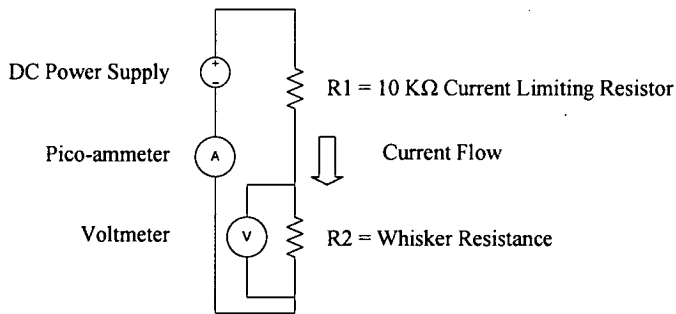


Fig. 4. Electrical schematic for the tin whisker test station

IV. EXPERIMENTAL RESULTS

A. Contact Resistance

The point at which a short occurs, when the film resistance breaks down, can easily be seen in Figure 6 when the current jumps from near zero, the nanoamp range, to the milliamp range.

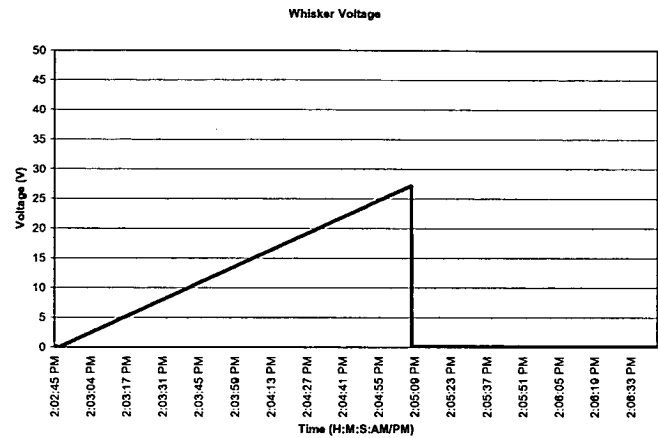


Fig. 5. Whisker voltage as a function of time plotted for whisker number 32, illustrating a single transition point.

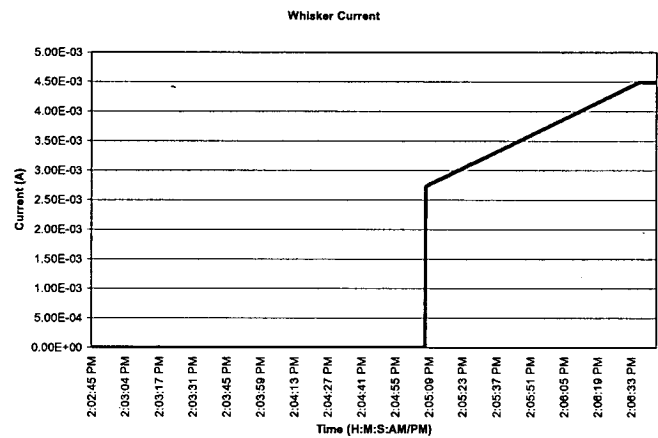


Fig. 6. Whisker current as a function of time plotted for whisker number 32, illustrating a single transition point.

Prior to breakdown the majority of the voltage drop is across the whisker due to the high resistance of the oxide film on the whisker. In this state, the whisker voltage reading tracks close to the power supply voltage. The power supply voltage increases linearly from 0 to 45 vdc, then it remains at 45 vdc for a few seconds at the end of the run until the software is given a stop command. After the film has broken down, the majority of the voltage drop is across the current limiting resistor. In this state, the low whisker voltage reading determined the small resistance of the whisker, card guide and micromanipulator. Refer to Figures 4 and 5.

Although the software had originally been written to stop recording data after the film resistance broke down as determined by the change in whisker current, it was decided to run 35 whiskers to the full range of the test, 0 – 45 vdc, to observe their behavior.

An interesting benefit of running the test from 0 - 45 vdc for all of the whiskers was the opportunity to witness the difference in transitions. A single transition point as illustrated in Figures 5 and 6, was exhibited by 20 of the 35 whiskers tested. Multiple transition points, as shown in Figures 7 and 8, were found in 9 of the 35 whiskers tested.

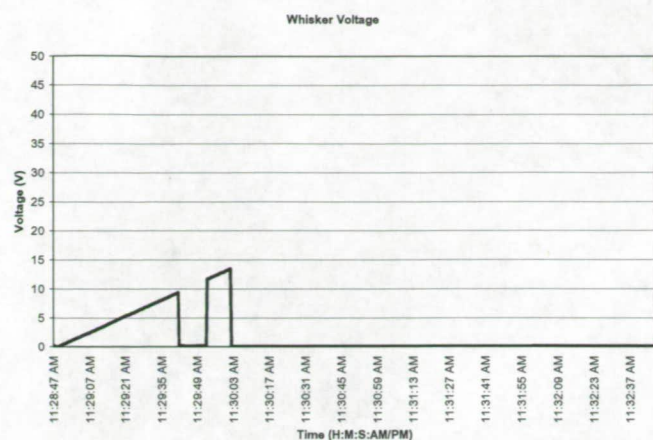


Fig. 7 Whisker voltage as a function of time plotted for whisker number 4, illustrating multiple transition points.

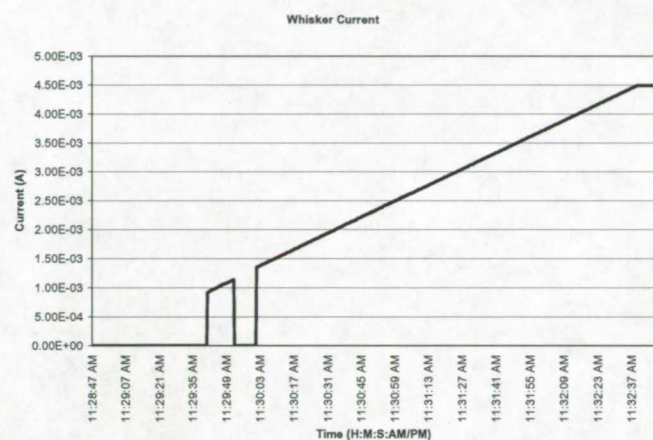


Fig. 8 Whisker current as a function of time plotted for whisker number 4, illustrating multiple transition points.

Multiple transitions with intermittent contact were present in 6 of the 35 whiskers tested. The intermittent contact may be explained by air currents in the room. Whiskers are very flexible and can appear to move like grass in the wind when observed under a microscope. Other possible explanations are that the probe was barely making contact with the whisker, or that thermal expansion caused whisker movement. An example of multiple transitions with intermittent contact is shown in Figures 9 and 10.

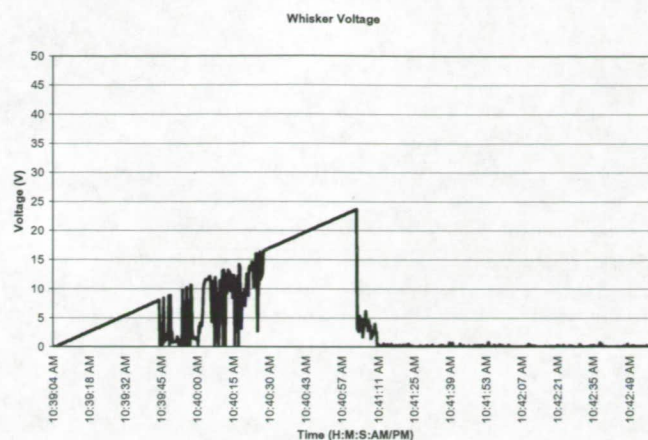


Fig. 9. Whisker voltage as a function of time plotted for whisker number 2, illustrating multiple transition points with intermittent contact.

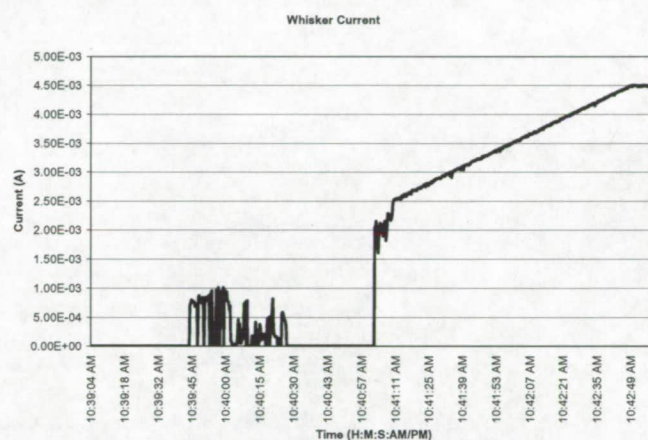


Fig. 10. Whisker current as a function of time plotted for whisker number 2, illustrating multiple transition points with intermittent contact.

For the tin whiskers that exhibited multiple transitions and multiple transitions with intermittency, the first occurrence of breakdown was recorded as the breakdown voltage for the whisker. This was chosen because the first time the whisker conducts current in the milliamp range it can cause a short circuit. The breakdown voltages for all thirty five whiskers are summarized in Table 1.

The whiskers 17 and 24 conducted up to 3.06 mA and 2.00 mA respectively before metallic conduction ceased. This result is likely caused by either vaporization of the whisker, or the whisker slipping away from the micromanipulator tip because the whisker was being touched too close to the end of the micromanipulator probe.

The voltage level at the transition to metallic conduction current, is the voltage level at which the film and oxide layers break down. The data is a table of breakdown voltage for each specimen.

Table 1
TIN WHISKER BREAKDOWN VOLTAGE DATA

Whisker Number	Transitions ^a	Whisker Voltage
1	S	33.57
2	M/I	7.99
3	M/I	3.39
4	M	9.29
5	M	3.08
6	M	15.68
7	S	13.48
8	S	8.49
9	M/I	13.57
10	S	2.09
11	M/I	10.69
12	S	1.89
13	S	10.09
14	M	28.17
15	M/I	8.38
16	M	4.29
17	M	29.27
18	S	38.96
19	S	18.09
20	S	22.49
21	S	22.49
22	S	18.89
23	S	5.09
24	M	9.59
25	S	5.68
26	M/I	8.48
27	S	28.48
28	S	4.58
29	S	44.05
30	M	8.89
31	M	8.79
32	S	27.18
33	S	14.79
34	S	21.28
35	S	34.77

^a The abbreviations in the transitions column are defined as follows: S = single transition, M = multiple transitions, M/I = multiple transitions with intermittent contact

From the data in Table 1, a cumulative distribution of the fraction of whiskers that have broken down vs. applied voltage is shown in Figure 11 as a stair step shaped plot.

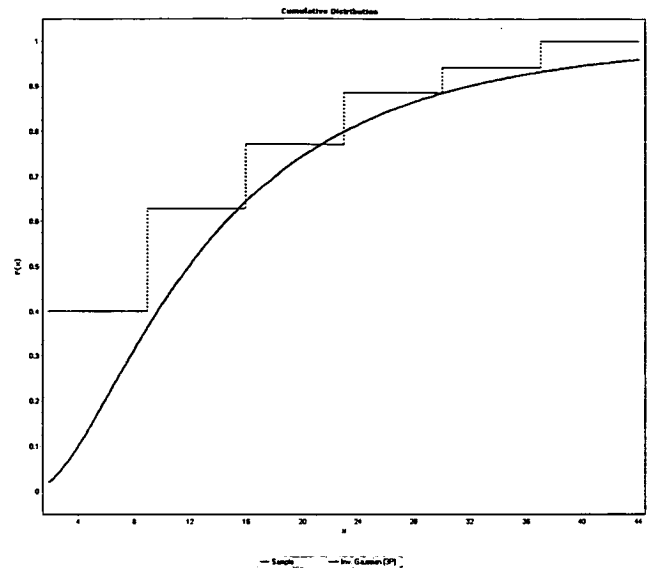


Fig. 11. Cumulative distribution of sample data and Inverse Gaussian (3-Parameter) model as a function of voltage.

The smoothed idealization of this is a cumulative probability function $F(x)$, estimating the probability that the whisker contact resistance, interrogated this way, will break down when the applied voltage has a given value. Then $f(x) = dF(x)/dx$ is the probability density for breakdown at x [33]. The applied voltage is represented here by the variable x . The breakdown voltages recorded above were analyzed using EasyFit® distribution fitting software to determine the probability distribution that best fits the data. The best fit cumulative probability function and probability density function are shown in Figures 11 and 12 respectively. The best fit distribution was the Inverse Gaussian (3-Parameter). A histogram of the data is also shown in Figure 12.

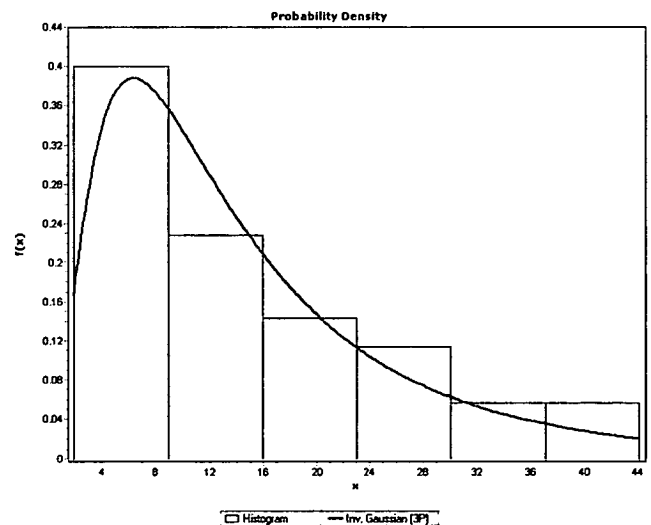


Fig. 12. Probability density function of Inverse Gaussian (3-Parameter) model as a function of voltage with a histogram of the sample data.

One tool to determine how well a specific model fits the observed data is the P-P plot shown in Figure 13. The closer the plot is to being linear, the better the model fits the observed data [34]. While the P-P plots help us weed out the distributions that don't fit well, it is often difficult to discern between the good fitting models when the plots are close in the degree of deviation from linearity. The Kolmogorov-Smirnov test will help us further analyze the best fit.

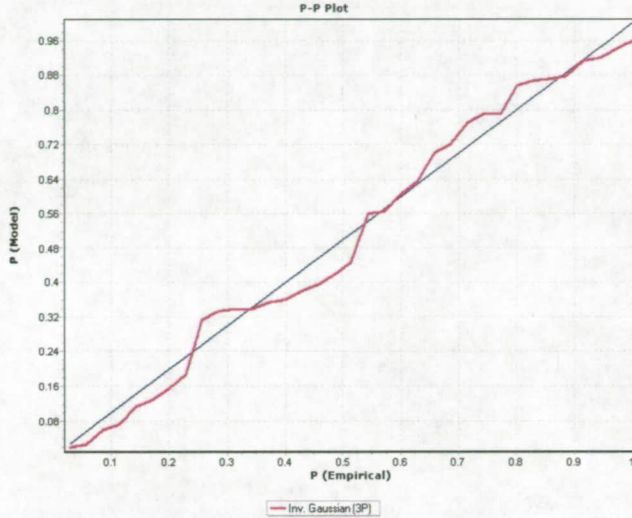


Fig. 13. The probability-probability (P-P) plot shows how well the data follows the Inverse Gaussian (3-Parameter) distribution.

The results of the Kolmogorov-Smirnov goodness of fit test are shown in Table 2. The null and alternative hypotheses for this test are: H_0 : The data follows the specified distribution, H_A : The data does not follow the specified distribution [34]. At the specified level of significance α , if the test statistic is greater than the critical value, the null hypothesis is rejected. For the values of α given below, we do not reject the null hypothesis.

Table 2
KOLMOGOROV-SMIRNOV TEST

Sample Size	35
Statistic	0.06676
Rank	1

α	Critical Value	Reject?
0.2	0.18086	No
0.15	0.1927	No
0.1	0.20622	No
0.05	0.22988	No
0.01	0.27552	No

The EasyFit® distribution fitting software tested over 40 different distributions before selecting the 3-Parameter Inverse Gaussian as the best fit based on the Komologrov-Smirnov test results.

The parameters for the Three Parameter Inverse Gaussian Distribution are $\lambda = 31.977$, $\mu = 17.571$, $\gamma = -1.9716$. The Probability Density Function for the Three Parameter Inverse Gaussian Distribution is shown in Equation 1.4 [34]:

$$f(x) = \sqrt{\frac{\lambda}{2\pi(x-\gamma)^3}} \exp\left(-\frac{\lambda(x-\gamma-\mu)^2}{2\mu^2(x-\gamma)}\right) \quad (1.4)$$

The Cumulative Distribution Function for the Three Parameter Inverse Gaussian Distribution is shown in Equation 1.5, where $\Phi(\cdot)$ is the normal cumulative distribution function [34]:

$$F(x) = \Phi\left(\sqrt{\frac{\lambda}{x-\gamma}}\left(\frac{x-\gamma}{\mu}-1\right)\right) + \Phi\left(-\sqrt{\frac{\lambda}{x-\gamma}}\left(\frac{x-\gamma}{\mu}+1\right)\right) \exp(2\lambda/\mu) \quad (1.5)$$

Based on our data, the expected (mean) voltage where a short will occur for the Three Parameter Inverse Gaussian Distribution is $\mu - \gamma = 15.5994$ vdc, with a variance of $\mu^3/\lambda = 169.6491$ [35].

It is important to note this distribution brings us closer to understanding the probability of a free whisker shorting across two exposed contacts. We have demonstrated that whisker shorting can be represented as a function of breakdown voltage. However, it is important to consider the limitations of the experiment including the small sample size, the number of conducting surfaces, and the difference and variation between force applied by gravity and the force applied by the micromanipulator probe.

Given that the density of tin is 7300 kg/m^3 [25], for a whisker that has a diameter of $2 \mu\text{m}$, length of 4mm ; the whisker volume will be $1.25\text{E-}14 \text{ m}^3$. The whisker volume multiplied by the density of tin gives the whisker mass of $m = 9.17\text{E-}11 \text{ kg}$. Since $F = ma$ and $a = 9.806\text{m/s}^2$ [36], we can calculate the force of gravity on the whisker to be $F = 9.0\text{E-}10 \text{ N}$. Since load applied to a whisker at each point of contact $P = F/2 = 4.50\text{E-}10 \text{ N}$ as illustrated in Figure 14.

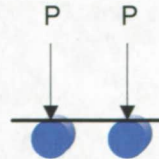


Fig. 14. Load Applied to Whisker Lying Across Two Conductors

The force applied by the micromanipulator probe to the whisker was calculated above as $P = 5.95\text{E-}10 \text{ N}$. The force applied to the micromanipulator was greater than that applied by gravity $P = 4.50\text{E-}10 \text{ N}$. The additional pressure was not enough to physically breach the oxide layer or we would have had breakdown voltages much closer to 0 vdc . However, the difference in pressure could cause a shift in the mean of the

distribution. A larger sample experiment with additional experimental controls will be performed in our future work.

B. Focused Ion Beam (FIB) Analysis

Tin whiskers from the same card guide used in the breakdown voltage experiment were cross-sectioned using an FEI 200 TEM FIB with a 30kV Gallium liquid metal ion source. The whiskers were removed from the card guide, placed on a microscopy stub using carbon tape, and then sputter coated with gold-palladium. Platinum was deposited on the region of interest prior to FIB sectioning in order to preserve the whisker's outer surface. It was observed that the whisker exhibited a fluted shape resembling an extruded surface, as shown in Figure 15. The ion beam was used to mill away whisker material until the desired region of interest to obtain a cross section normal to the whisker's growth direction, Figure 16.

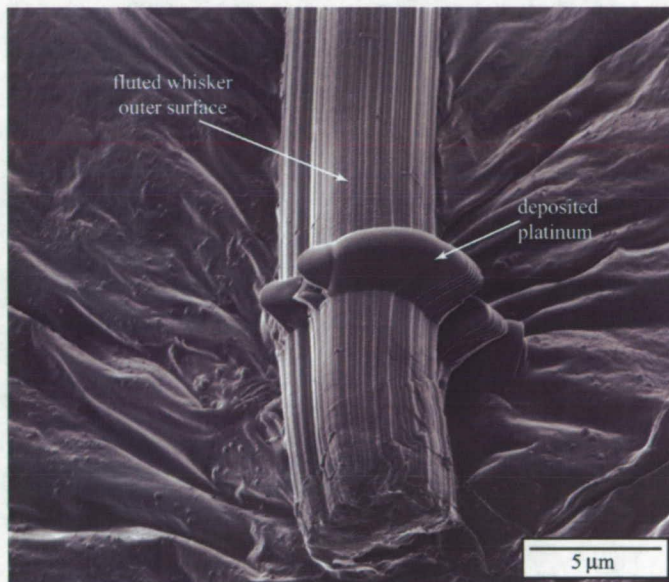


Fig. 15. FIB image of tin whisker removed from card guide shows a fluted outer surface. Platinum was deposited on the surface prior to sectioning in order to preserve the region of interest (NASA/UCF).

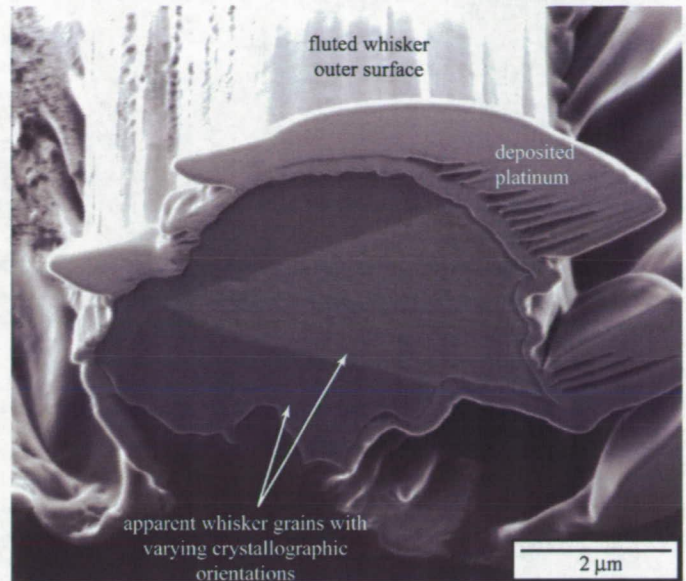


Fig. 16. FIB image of as-sectioned tin whisker shows apparent variation in grain orientation within the cross-section. Image was taken at a 52° angle from horizontal (NASA/UCF).

The FIB cross section facilitates the examination of what appears to be grains with varying crystallographic orientations within the tin whisker as illustrated in Figure 16. The polycrystalline nature of the whiskers will be verified in the Part II experiment using transmission electron microscopy (TEM). The image in Figure 16 was taken at a 52° tilt resulting in the semi-elliptical shape. However, the geometry of the cross-section is expected to be more circular. The diameter of the tin whisker is approximately 6.7 μm in the vertical direction and 6.1 μm in the horizontal direction.

An additional two whiskers from the card guide were removed and sectioned by the FIB. These smaller-diameter whiskers exhibited the commonly reported single crystal structure as shown in Figure 17. The diameter of the top whisker is approximately 2.4 μm in the vertical direction and 2.0 μm in the horizontal direction. The diameter of the bottom whisker is approximately 1.7 μm in the vertical direction and 2.0 μm in the horizontal direction. Since the cross section of the each tin whisker was not truly circular, the diameter measurements given above were made along the largest dimension in the stated direction.

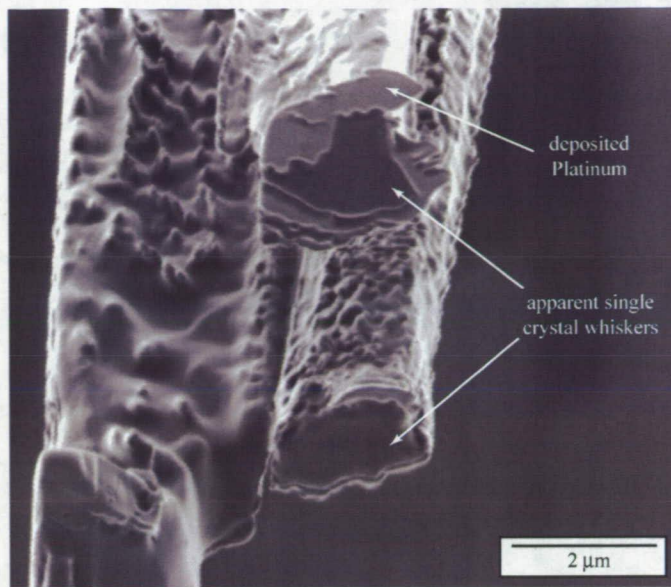


Fig. 17. FIB image of two as-sectioned tin whiskers that exhibited the expected single-crystal cross section. Image was taken 52° from horizontal (NASA/UCF).

V. CONCLUSIONS

In this experiment we developed an empirical probability model to quantify the probability of occurrence of an electrical short circuit from tin whiskers as a function of voltage. This model can be used to improve existing risk simulation models. We also obtained FIB images of a tin whisker with what appears to have two different crystal orientations. Our planned future work includes a larger sample experiment to improve the probability model, as well a TEM examination of the whisker to verify the different crystal orientations in a single whisker.

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